CY7C161A
CY7C162A

16K x 4 Static RAM with Separate I/O

Features

- **High speed**
  - **— 20 ns t_{AA}**
- **CMOS for optimum speed/power**
- **Transparent write (7C161A)**
- **Low active power**
  - **— 550 mW**
- **Low standby power**
  - **— 220 mW**
- **TTL-compatible inputs and outputs**
- **Automatic power-down when deselected**

Functional Description

The CY7C161A and CY7C162A are high-performance CMOS static RAMs organizes as 16,384 by 4 bits with separate I/O. Easy memory expansion is provided by active LOW chip enables ($\overline{CE}_1$, $\overline{CE}_2$) and three-state drivers. They have an automatic power-down feature, reducing the power consumption by 60% when deselected.

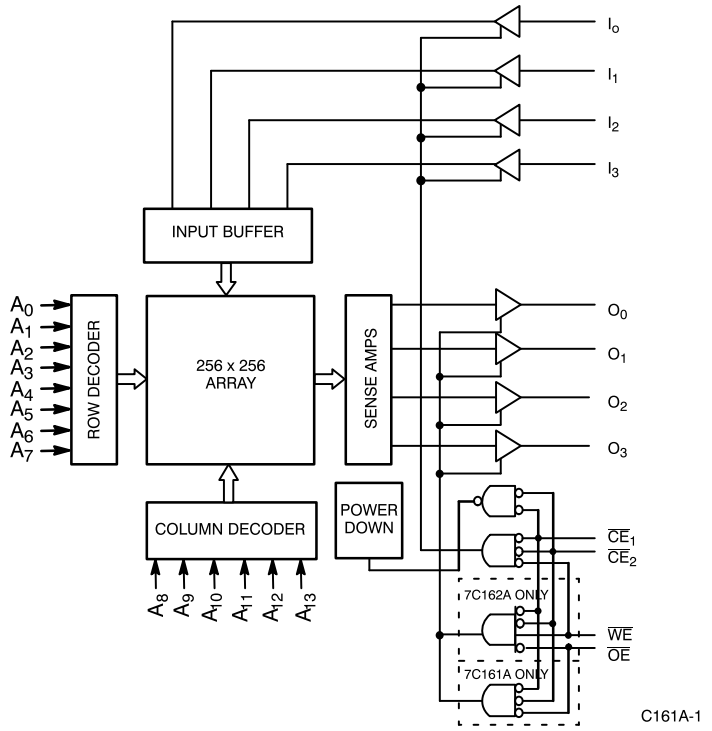
Writing to the device is accomplished when the chip enable ($\overline{CE}_1$, $\overline{CE}_2$) and write enable ($\overline{WE}$) inputs are both LOW. Data on the four input pins (I_0 through I_3) is written into the memory location specified on the address pins (A_0 through A_{13}).

Reading the device is accomplished by taking the chip enables ($\overline{CE}_1$, $\overline{CE}_2$) LOW while write enable ($\overline{WE}$) remains HIGH. Under these conditions the contents of the memory location specified on the address pins will appear on the four data output pins.

The output pins stay in high-impedance state when write enable ($\overline{WE}$) is LOW (7C162A only), or one of the chip enables ($\overline{CE}_1$, $\overline{CE}_2$) are HIGH.

A die coat is used to insure alpha immunity.

Logic Block Diagram



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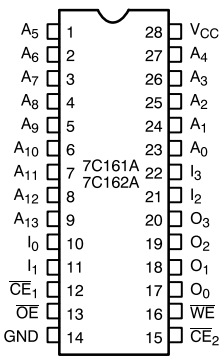
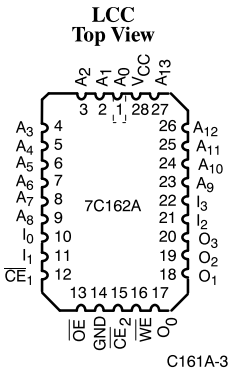
Pin Configurations

DIP
Top View



C161A-2

LCC
Top View



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Selection Guide[1]

		7C161A–15 7C162A–15	7C161A–20 7C162A–20	7C161A–25 7C162A–25	7C161A–35 7C162A–35
Maximum Access Time (ns)		15	20	25	35
Maximum Operating Current (mA)	Military	160	100	100	100
Maximum Standby Current (mA)	Military	40/20	40/20	40/20	30/20

Shaded area contains advanced information.

Note:
1. For commercial specifications, see the CY7C161/CY7C162 datasheet.

Maximum Ratings

(Above which the useful life may be impaired. For user guidelines, not tested.)

Storage Temperature ..... −65°C to +150°C

Ambient Temperature with Power Applied ..... −55°C to +125°C

Supply Voltage to Ground Potential (Pin 24 to Pin 12) ..... −0.5V to +7.0V

DC Voltage Applied to Outputs in High Z State[2] ..... −0.5V to +7.0V

DC Input Voltage[2] ..... −0.5V to +7.0V

Output Current into Outputs (LOW) ..... 20 mA

Static Discharge Voltage ..... >2001V (per MIL-STD-883, Method 3015)

Latch-Up Current ..... >200 mA

Operating Range

Range	Ambient Temperature	V_{CC}
Military[3]	−55°C to +125°C	5V ± 10%

Notes:

2. Minimum voltage is equal to −3.0V for pulse durations less than 30 ns.
3. T_A is the "instant on" case temperature.

Electrical Characteristics Over the Operating Range[4]

Parameter	Description	Test Conditions		7C161A−15 7C162A−15 Min.	7C161A−15 7C162A−15 Max.	7C161A−20 7C162A−20 Min.	7C161A−20 7C162A−20 Max.	Unit
V_{OH}	Output HIGH Voltage	V_{CC} = Min., I_{OH} = −4.0 mA		2.4		2.4		V
V_{OL}	Output LOW Voltage	V_{CC} = Min., I_{OL} = 8.0 mA			0.4		0.4	V
V_{IH}	Input HIGH Voltage			2.2	V_{CC}	2.2	V_{CC}	V
V_{IL}	Input LOW Voltage[2]			−0.5	0.8	−0.5	0.8	V
I_{IX}	Input Load Current	GND ≤ V_I ≤ V_{CC}		−5	+5	−5	+5	µA
I_{OZ}	Output Leakage Current	GND ≤ V_I ≤ V_{CC}, Output Disabled		−5	+5	−5	+5	µA
I_{OS}	Output Short Circuit Current[5]	V_{CC} = Max., V_{OUT} = GND			−350		−350	mA
I_{CC}	V_{CC} Operating Supply Current	V_{CC} = Max. I_{OUT} = 0 mA	Military		160		100	mA
I_{SB1}	Automatic $\overline{CE}$ Power-Down Current	Max. V_{CC}, $\overline{CE}$ ≥ V_{IH}, Min. Duty Cycle = 100%	Military		40		40	mA
I_{SB2}	Automatic $\overline{CE}$ Power-Down Current	Max. V_{CC}, $\overline{CE}_1$ ≥ V_{CC} − 0.3V, V_{IN} ≥ V_{CC} − 0.3V or V_{IN} ≤ 0.3V	Military		20		20	mA

Shaded area contains advanced information.

Electrical Characteristics Over the Operating Range[4] (continued)

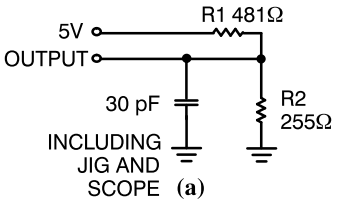
Parameter	Description	Test Conditions		7C161A−25 7C162A−25 Min.	7C161A−25 7C162A−25 Max.	7C161A−35 7C162A−35 Min.	7C161A−35 7C162A−35 Max.	Unit
V_{OH}	Output HIGH Voltage	V_{CC} = Min., I_{OH} = −4.0 mA		2.4		2.4		V
V_{OL}	Output LOW Voltage	V_{CC} = Min., I_{OL} = 8.0 mA			0.4		0.4	V
V_{IH}	Input HIGH Voltage			2.2	V_{CC}	2.2	V_{CC}	V
V_{IL}	Input LOW Voltage[2]			−0.5	0.8	−0.5	0.8	V
I_{IX}	Input Load Current	GND ≤ V_I ≤ V_{CC}		−5	+5	−5	+5	µA
I_{OZ}	Output Leakage Current	GND ≤ V_I ≤ V_{CC}, Output Disabled		−5	+5	−5	+5	µA
I_{OS}	Output Short Circuit Current[5]	V_{CC} = Max., V_{OUT} = GND			−350		−350	mA
I_{CC}	V_{CC} Operating Supply Current	V_{CC} = Max., I_{OUT} = 0 mA	Military		100		100	mA
I_{SB1}	Automatic $\overline{CE}$ Power-Down Current	Max. V_{CC}, $\overline{CE}$ ≥ V_{IH}, Min. Duty Cycle = 100%	Military		40		30	mA
I_{SB2}	Automatic $\overline{CE}$ Power-Down Current	Max. V_{CC}, $\overline{CE_1}$ ≥ V_{CC} − 0.3V, V_{IN} ≥ V_{CC} − 0.3V or V_{IN} ≤ 0.3V	Military		20		20	mA

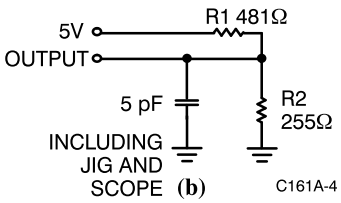
Capacitance[6]

Parameter	Description	Test Conditions	Max.	Unit
C_{IN}	Input Capacitance	T_A = 25°C, f = 1 MHz, V_{CC} = 5.0V	10	pF
C_{OUT}	Output Capacitance		10	pF

Notes:
4. See the last page of this specification for Group A subgroup testing information.
5. Not more than 1 output should be shorted at one time. Duration of the short circuit should not exceed 30 seconds.
6. Tested initially and after any design or process changes that may affect these parameters.

AC Test Loads and Waveforms





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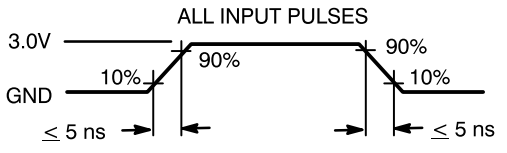
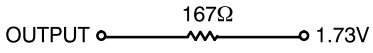


C161A-5

Equivalent to: THÉVENIN EQUIVALENT



Switching Characteristics Over the Operating Range[4, 7, 8]

Parameter	Description	7C161A−15 7C162A−15		7C161A−20 7C162A−20		7C161A−25 7C162A−25		7C161A−35 7C162A−35		Unit
		Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
READ CYCLE										
t_{RC}	Read Cycle Time	15		20		25		35		ns
t_{AA}	Address to Data Valid		15		20		25		35	ns
t_{OHA}	Output Hold from Address Change	3		5		5		5		ns
t_{ACE}	$\overline{CE}$ LOW to Data Valid		15		20		25		35	ns
t_{DOE}	$\overline{OE}$ LOW to Data Valid		7		10		12		15	ns
t_{LZOE}	$\overline{OE}$ LOW to LOW Z	0		3		3		3		ns
t_{HZOE}	$\overline{OE}$ HIGH to HIGH Z		8		8		10		12	ns
t_{LZCE}	$\overline{CE}$ LOW to Low Z[9]	3		5		5		5		ns
t_{HZCE}	$\overline{CE}$ HIGH to High Z[9, 10]		8		8		10		15	ns
t_{PU}	$\overline{CE}$ LOW to Power-Up	0		0		0		0		ns
t_{PD}	$\overline{CE}$ HIGH to Power-Down		15		20		20		20	ns
WRITE CYCLE[11]										
t_{WC}	Write Cycle Time	15		20		20		25		ns
t_{SCE}	$\overline{CE}$ LOW to Write End	10		15		20		25		ns
t_{AW}	Address Set-Up to Write End	10		15		20		25		ns
t_{HA}	Address Hold from Write End	0		0		0		0		ns
t_{SA}	Address Set-Up to Write Start	0		0		0		0		ns
t_{PWE}	$\overline{WE}$ Pulse Width	10		15		15		20		ns
t_{SD}	Data Set-Up to Write End	7		10		10		15		ns
t_{HD}	Data Hold from Write End	0		0		0		0		ns
t_{LZWE}	$\overline{WE}$ HIGH to Low Z[9] (7C162A)	3		5		5		5		ns
t_{HZWE}	$\overline{WE}$ LOW to High Z[9, 10] (7C162A)		7		7		7		10	ns
t_{DWE}	$\overline{WE}$ LOW to Data Valid (7C161A)		15		20		25		30	ns
t_{ADV}	Data Valid to Output Valid (7C161A)		15		20		20		30	ns
t_{DCE}	$\overline{CE}$ LOW to Data Valid (7C161A)		15		20		25		35	ns

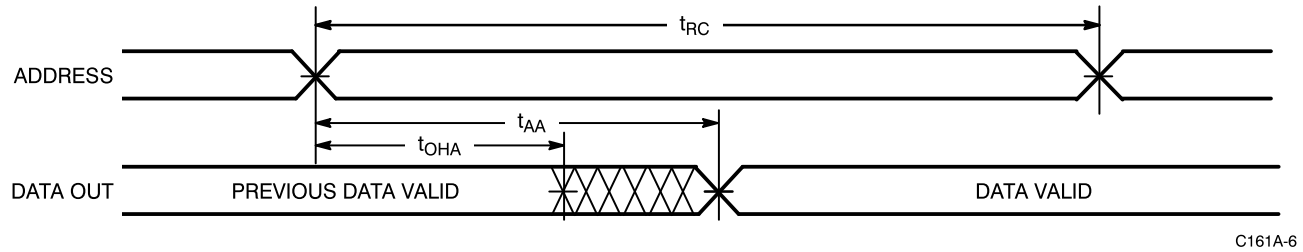
Shaded area contains advanced information.

Notes:

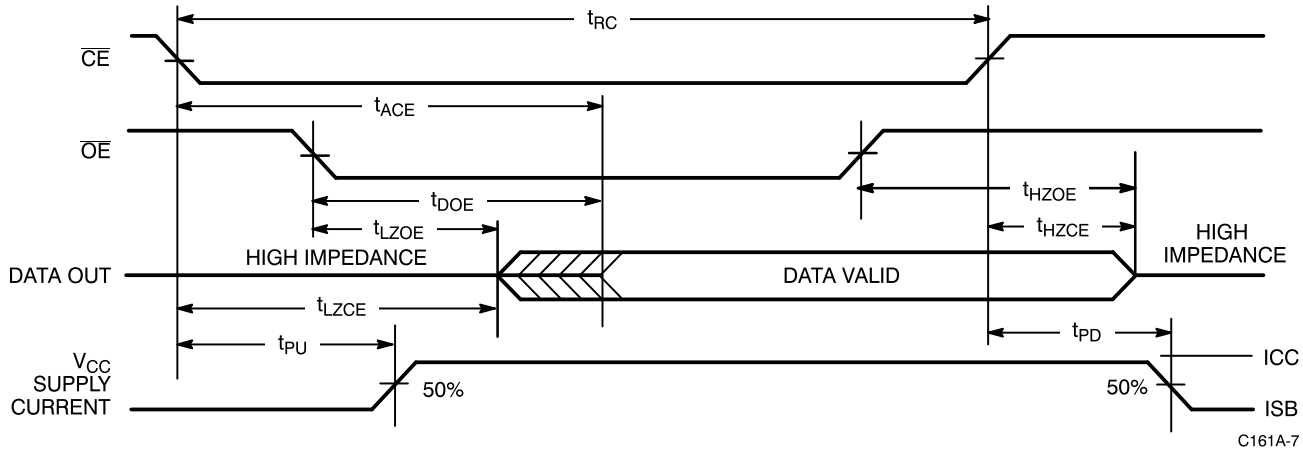
7. Test conditions assume signal transition time of 5 ns or less, timing reference levels of 1.5V, input pulse levels of 0 to 3.0V, and output loading of the specified I_{OL}/I_{OH} and 30-pF load capacitance.
8. Both $\overline{CE}_1$ and $\overline{CE}_2$ are represented by $\overline{CE}$ in the Switching Characteristics and Waveforms sections.
9. At any given temperature and voltage condition, t_{HZ} is less than t_{LZ} for any given device.
10. t_{HZCE} and t_{HZWE} are specified with $C_L = 5$ pF as in part (b) of AC Test Loads and Waveforms. Transition is measured ±500 mV from steady-state voltage.
11. The internal write time of the memory is defined by the overlap of $\overline{CE}_1$ LOW, $\overline{CE}_2$ LOW, and $\overline{WE}$ LOW. Both signals must be LOW to initiate a write and either signal can terminate a write by going HIGH. The data input set-up and hold timing should be referenced to the rising edge of the signal that terminates the write.

Switching Waveforms[8]

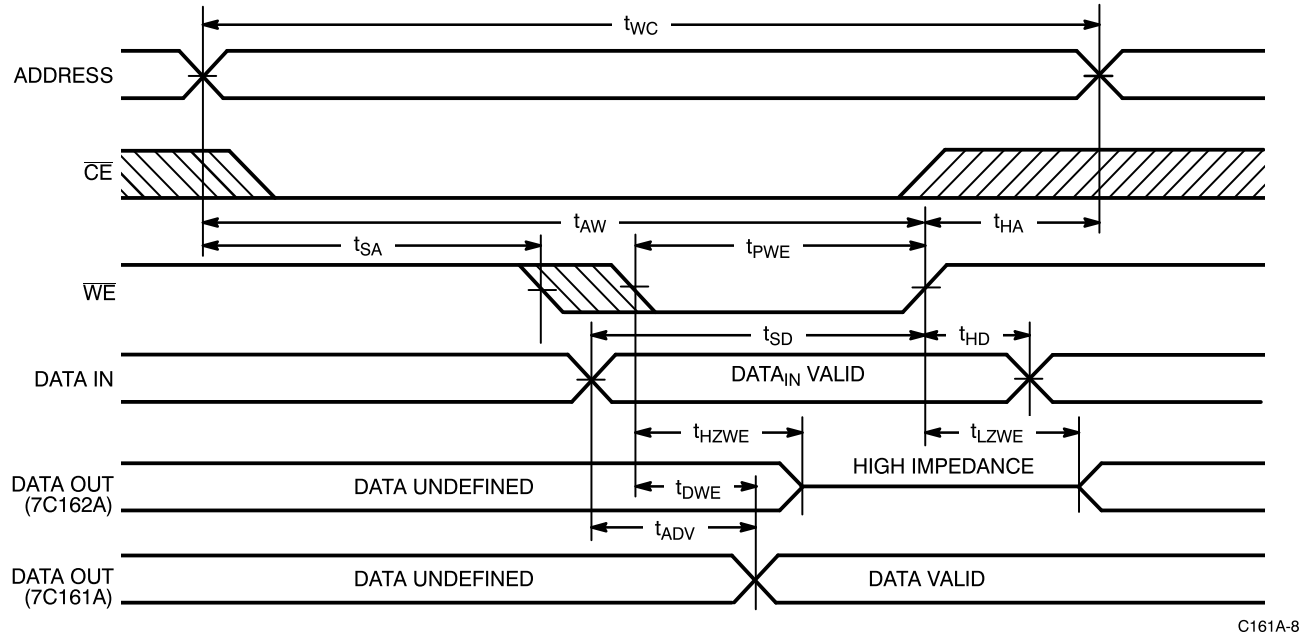
Read Cycle No. 1[12, 13]



Read Cycle No. 2[12, 14]



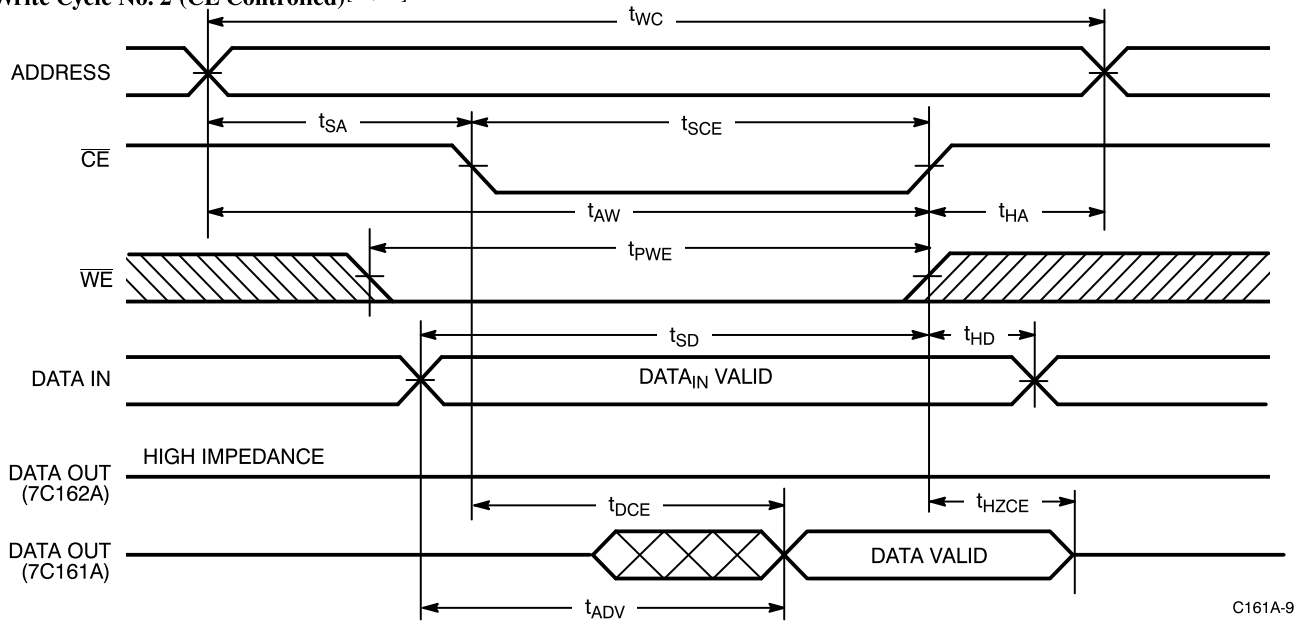
Write Cycle No. 1 ($\overline{WE}$ Controlled)[11]



Notes:
12. $\overline{WE}$ is HIGH for read cycle.
13. Device is continuously selected, $\overline{CE}_1$, $\overline{CE}_2$ = V_{IL}.
14. Address valid prior to or coincident with $\overline{CE}_1$, $\overline{CE}_2$ transition LOW.

Switching Waveforms (continued)

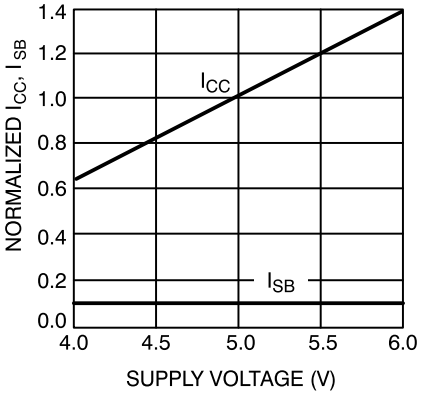
Write Cycle No. 2 ($\overline{CE}$ Controlled)[11, 15]



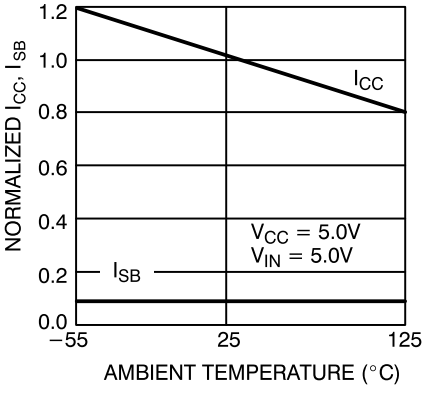
Note:
15. If $\overline{CE}$ goes HIGH simultaneously with $\overline{WE}$ HIGH, the output remains in a high-impedance state (7C162A only).

Typical DC and AC Characteristics

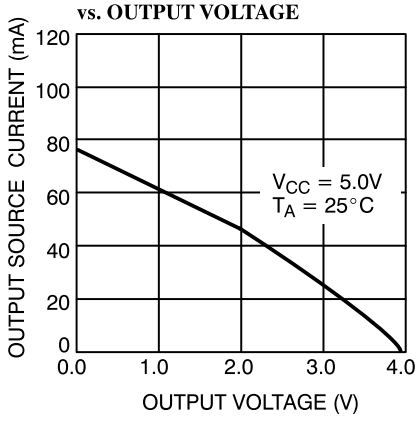
NORMALIZED SUPPLY CURRENT vs. SUPPLY VOLTAGE



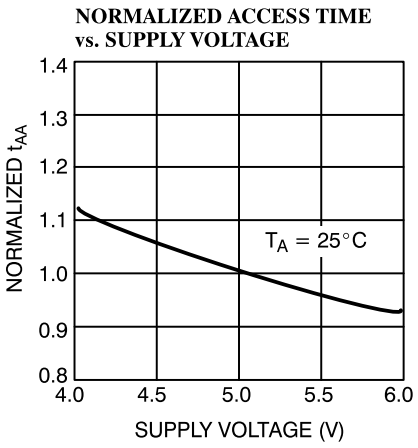
NORMALIZED SUPPLY CURRENT vs. AMBIENT TEMPERATURE

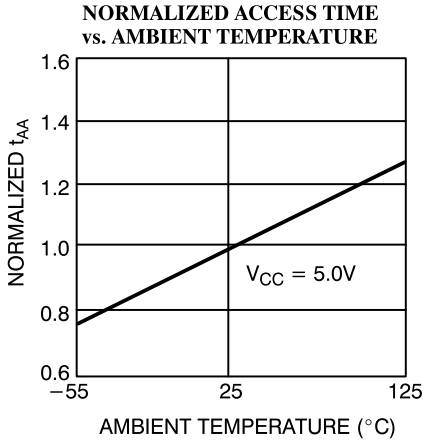


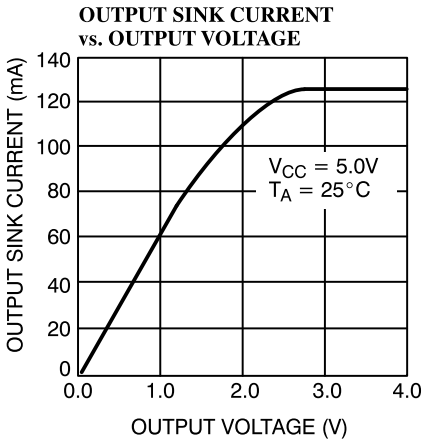
OUTPUT SOURCE CURRENT vs. OUTPUT VOLTAGE

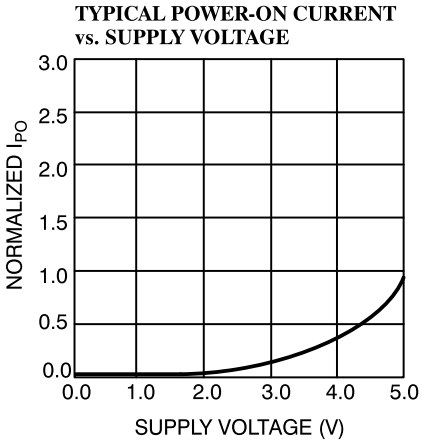


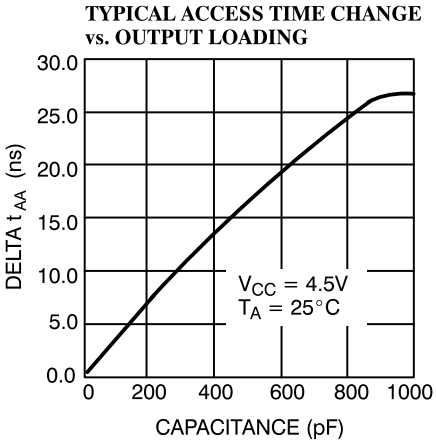
Typical DC and AC Characteristics (continued)

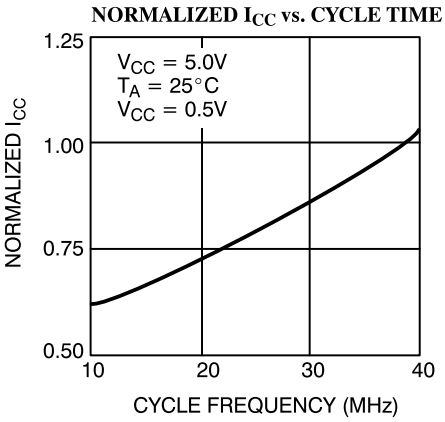












Address Designators

Address Name	Address Function	Pin Number
A5	X3	1
A6	X4	2
A7	X5	3
A8	X6	4
A9	X7	5
A10	Y0	6
A11	Y1	7
A12	Y5	8
A13	Y4	9
A0	Y3	23
A1	Y2	24
A2	X0	25
A3	X1	26
A4	X2	27

Ordering Information

Speed (ns)	Ordering Code	Package Name	Package Type	Operating Range
15	CY7C161A−15DMB	D22	28-Lead (300-Mil) CerDIP	Military
20	CY7C161A−20DMB	D22	28-Lead (300-Mil) CerDIP	Military
25	CY7C161A−25DMB	D22	28-Lead (300-Mil) CerDIP	Military
35	CY7C161A−35DMB	D22	28-Lead (300-Mil) CerDIP	Military

Speed (ns)	Ordering Code	Package Name	Package Type	Operating Range
15	CY7C162A−15DMB	D22	28-Lead (300-Mil) CerDIP	Military
	CY7C162A−15LMB	L54	28-Pin Rectangular Leadless Chip Carrier	
20	CY7C162A−20DMB	D22	28-Lead (300-Mil) CerDIP	Military
	CY7C162A−20LMB	L54	28-Pin Rectangular Leadless Chip Carrier	
25	CY7C162A−25DMB	D22	28-Lead (300-Mil) CerDIP	Military
	CY7C162A−25LMB	L54	28-Pin Rectangular Leadless Chip Carrier	
35	CY7C162A−35DMB	D22	28-Lead (300-Mil) CerDIP	Military
	CY7C162A−35LMB	L54	28-Pin Rectangular Leadless Chip Carrier	

Shaded areas contain advanced information.

MILITARY SPECIFICATIONS
Group A Subgroup Testing

DC Characteristics

Parameter	Subgroups
V_{OH}	1, 2, 3
V_{OL}	1, 2, 3
V_{IH}	1, 2, 3
V_{IL} Max.	1, 2, 3
I_{IX}	1, 2, 3
I_{OZ}	1, 2, 3
I_{OS}	1, 2, 3
I_{CC}	1, 2, 3
I_{SB1}	1, 2, 3
I_{SB2}	1, 2, 3

Switching Characteristics

Parameter	Subgroups
READ CYCLE	
t_{RC}	7, 8, 9, 10, 11
t_{AA}	7, 8, 9, 10, 11
t_{OHA}	7, 8, 9, 10, 11
t_{ACE}	7, 8, 9, 10, 11
t_{DOE}	7, 8, 9, 10, 11
WRITE CYCLE	
t_{WC}	7, 8, 9, 10, 11
t_{SCE}	7, 8, 9, 10, 11
t_{AW}	7, 8, 9, 10, 11
t_{HA}	7, 8, 9, 10, 11
t_{SA}	7, 8, 9, 10, 11
t_{PWE}	7, 8, 9, 10, 11
t_{SD}	7, 8, 9, 10, 11
t_{HD}	7, 8, 9, 10, 11
t_{DWE}[16]	7, 8, 9, 10, 11
t_{ADV}	7, 8, 9, 10, 11

Notes:
16. 7C161A only.

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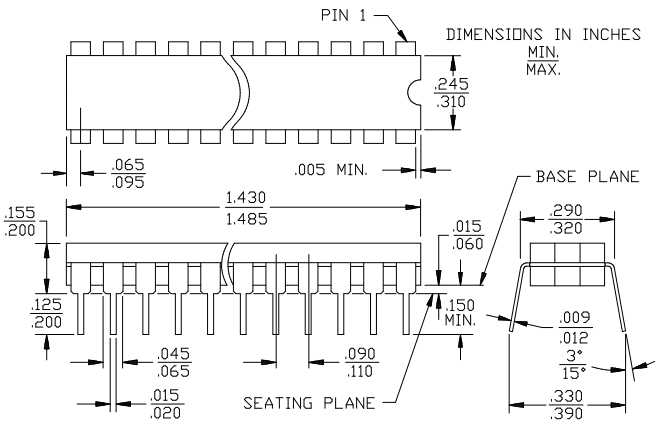
Package Diagrams

28-Lead (300-Mil) CerDIP D22
MIL−STD−1835 D−15 Config. A



28-Pin Rectangular Leadless Chip Carrier L54
MIL−STD−1835 C−11A